

Please replace the paragraph beginning on page 32, line 24, with the following:

In accordance with Examples 12 and 13, 1000 kinds of optical disks were manufactured in which the composition is represented by $[(\text{Ge} + \text{Sn})_4\text{Sb}_2\text{Te}_7]_{(100y-z)}\text{Cr}_y\text{Ag}_z$. In the composition, x indicates a percentage of Sn in the entire composition and y and z indicate atom%. The values of x, y and z were varied in the following range:

x = 0, 1, 2, 3, 4, 5, 8, 10, 15, 20%

y = 0, 1, 2, 3, 4, 5, 8, 10, 15, 20%

z = 0, 1, 2, 3, 4, 5, 8, 10, 15, 20%.

The thickness of the respective layers and evaluation criteria are identical to those of Examples 12 and 13. It was confirmed that equivalent or better performance was obtainable for all the three criteria when the Sn concentration was in a range from 3% to 15%, the Cr concentration was in a range from 1% to 5%, and the Ag concentration was in a range from 1% to 10%. It was effective especially in improving signal amplitude, stability of rewiring sensitivity and repeatability when the Sn concentration was in a range from 5% to 10%, the Cr concentration was in a range from 1% to 3%, and the Ag concentration was in a range from 1% to 3%.

IN THE CLAIMS

Please amend the following claim:

10. (Amended) The information recording medium according to claim 9, wherein the crystal structure comprising the lattice defect further comprises at least one combination of elements selected from Sn-Cr, Sn-Mn, Sn-Ag, Mn-Ag, Cr-Ag, and Sn-Cr-Ag.